

INFORMATION DISCLOSURE CITATION

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ATTY DOCKET NO.

WLJ.071

SERIAL NO.

09/744,212

Jyoti Kiron BHARDWAJ

FILING

01/22/01

GROUP

1746 1765

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
qd	A	5,221,366	06/22/93	ROBERTS ET AL.	148	22	—
	B	5,213,621	05/25/93	IVANKOVITS ET AL.	134	3	—
	C	5,213,622	05/25/93	BOHLING ET AL.	134	3	—
	D	4,579,623	04/01/86	SUZUKI ET AL.	165	626	—
	E	4,529,475	07/16/85	OKANO ET AL.	156	643	—
	F	4,749,440	06/07/88	BLACKWOOD ET AL.	156	646	—
qd	G	4,857,142	08/15/89	SYVERSON	156	646	—

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
qd	H	WO 94/14187	06/23/94	PCT	—	—	✓	
qd	I	DE 4317274 A1	12/01/94	GERMANY	—	—		✓
qd	J	DE 19704454 A1	08/20/98	GERMANY	—	—		✓

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

qd	K	C. Rinn Cleavelin et al., "Silicon Dioxide Removal in Anhydrous HF Gas," November 1987, Semiconductor International, pages 95-99.
qd	L	D.L. Flamm et al., "Plasma etching," Chemistry of the Semiconductor Industry, pages 343 - 390.

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INFORMATION DISCLOSURE CITATION

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Docket Number (Optional)

WLJ.071

Application Number

09/744,212

Applicant(s)

Jyoti Kiron BHARDWAJ

Filing Date

01/22/01

Group Art Unit

1746 1265

*EXAMINER

INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Butterbaugh et al., "Gas-Phase Etching of Silicon Oxide with Anhydrous HF and Isopropanol," Proceedings Electrochemical Soc. PV 1994, pages 374-383.

K. Torek et al., "Reduced Pressure etching of Thermal Oxides in Anhydrous HF/Alcoholic Gas Mixtures," J. Electrochem. Soc., vol. 142, no. 4, April 1995, pages 1322-1326.

M. Wong et al., "Silicon Etch Using Vapor Phase HF/F2O and O3," J. Electrochem. Soc., Vol. 140, no. 2, February 1993, pages 567-570.

Chun Su Lee et al., "Modeling and Characterization of Gas-Phase Etching of Thermal Oxide and TEOS Oxide Using Anhydrous HF and CH3OH," J. Electrochem. Soc., Vol. 143, No. 3, March 1996, pages 1099 - 1103.

Kirt R. Williams et al., "Etch Rates for Micromachining Processing," Journal of Microelectromechanical Systems, Vol. 5, No. 4, December 1996, pages 256 - 269.

Gregory T. A. Kovacs et al., "Bulk Micromachining of Silicon," Proceedings of the IEEE, Vol. 86, No. 8, August 1998, pages 1536-1551.

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